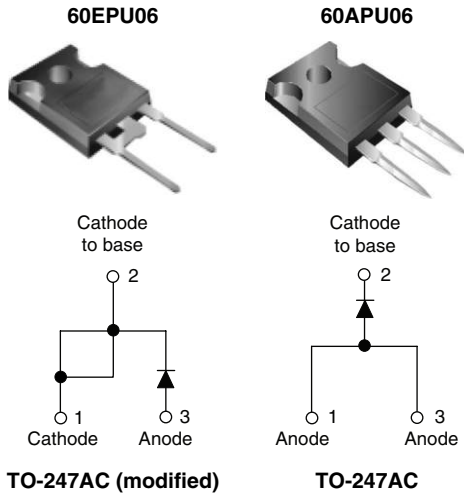


Ultrafast Soft Recovery Diode, 60 A FRED Pt™



FEATURES

- Ultrafast recovery
- 175 °C operating junction temperature
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

PRODUCT SUMMARY

| | |
|--------------------|-------|
| t_{rr} (typical) | 34 ns |
| $I_{F(AV)}$ | 60 A |
| V_R | 600 V |

ABSOLUTE MAXIMUM RATINGS

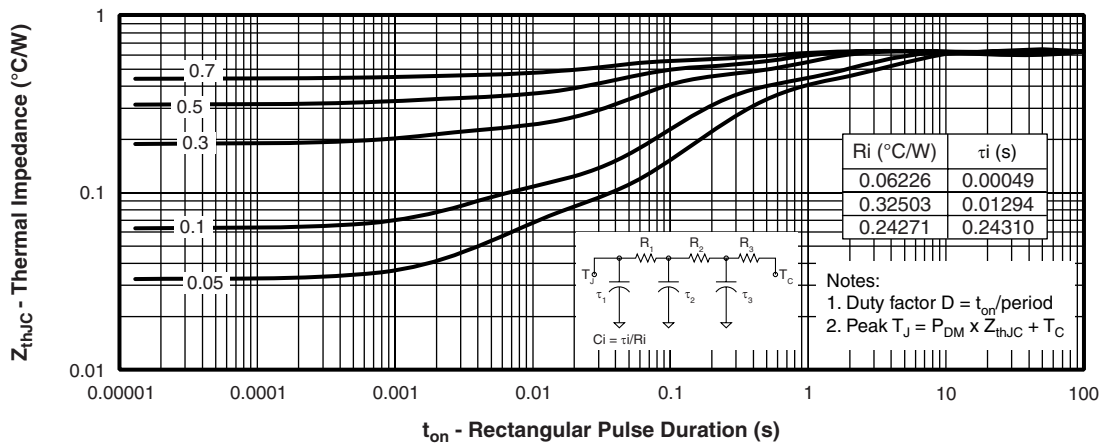
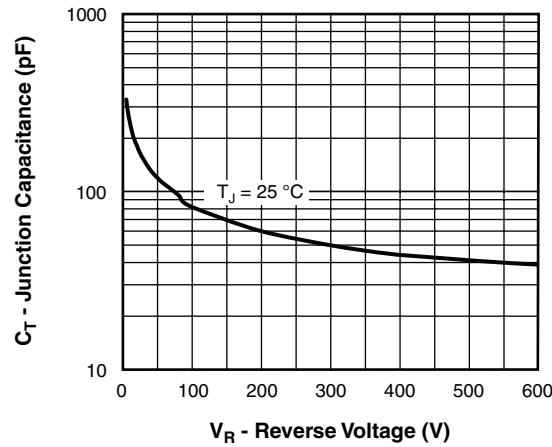
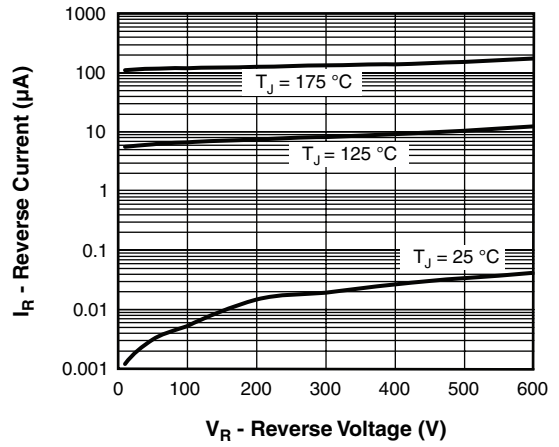
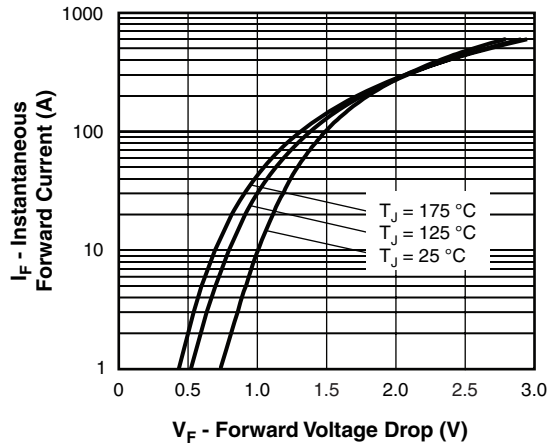
| PARAMETER | SYMBOL | TEST CONDITIONS | MAX. | UNITS |
|---|----------------|-----------------------|-------------|-------|
| Cathode to anode voltage | V_R | | 600 | V |
| Continuous forward current | $I_{F(AV)}$ | $T_C = 116\text{ °C}$ | 60 | A |
| Single pulse forward current | I_{FSM} | $T_C = 25\text{ °C}$ | 600 | |
| Maximum repetitive forward current | I_{FRM} | Square wave, 20 kHz | 120 | |
| Operating junction and storage temperatures | T_J, T_{Stg} | | - 55 to 175 | °C |

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|-------------------------------------|---------------|---|------|------|------|---------------|
| Breakdown voltage, blocking voltage | V_{BR}, V_r | $I_R = 100\ \mu\text{A}$ | 600 | - | - | V |
| Forward voltage | V_F | $I_F = 60\text{ A}$ | - | 1.35 | 1.68 | |
| | | $I_F = 60\text{ A}, T_J = 125\text{ °C}$ | - | 1.20 | 1.42 | |
| | | $I_F = 60\text{ A}, T_J = 175\text{ °C}$ | - | 1.11 | 1.30 | |
| Reverse leakage current | I_R | $V_R = V_R\text{ rated}$ | - | - | 50 | μA |
| | | $T_J = 150\text{ °C}, V_R = V_R\text{ rated}$ | - | - | 500 | |
| Junction capacitance | C_T | $V_R = 600\text{ V}$ | - | 39 | - | pF |

| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified) | | | | | | | |
|--|-----------|---|-----------------------------------|------|------|-------|----|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Reverse recovery time | t_{rr} | $I_F = 1\text{ A}$, $dI_F/dt = 200\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$ | - | 34 | 45 | ns | |
| | | $T_J = 25\text{ }^\circ\text{C}$ | - | 81 | - | | |
| | | $T_J = 125\text{ }^\circ\text{C}$ | - | 164 | - | | |
| Peak recovery current | I_{RRM} | $I_F = 60\text{ A}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$ | $T_J = 25\text{ }^\circ\text{C}$ | - | 7.4 | - | A |
| | | | $T_J = 125\text{ }^\circ\text{C}$ | - | 17.0 | - | |
| Reverse recovery charge | Q_{rr} | $I_F = 60\text{ A}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$ | $T_J = 25\text{ }^\circ\text{C}$ | - | 300 | - | nC |
| | | | $T_J = 125\text{ }^\circ\text{C}$ | - | 1394 | - | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|------------|--|-------------|------|-------------|---------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Thermal resistance, junction to case | R_{thJC} | | - | - | 0.63 | K/W |
| Thermal resistance, case to heatsink | R_{thCS} | Mounting surface, flat, smooth and greased | - | 0.2 | - | |
| Weight | | | - | 5.5 | - | g |
| | | | - | 0.2 | - | oz. |
| Mounting torque | | | 1.2 (10) | - | 2.4 (20) | N · m (lbf · in) |
| Marking device | | Case style TO-247AC modified | 60EPU06 | | | |
| | | Case style TO-247AC | 60APU06 | | | |



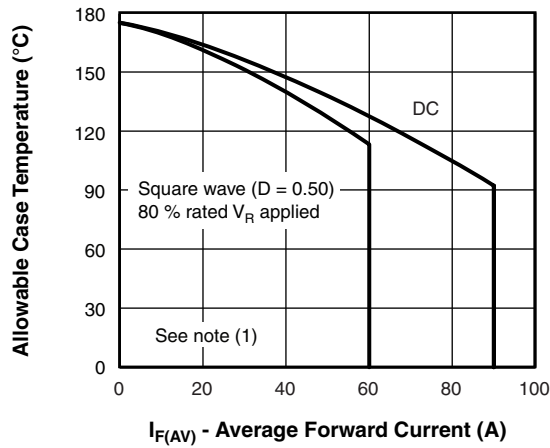


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

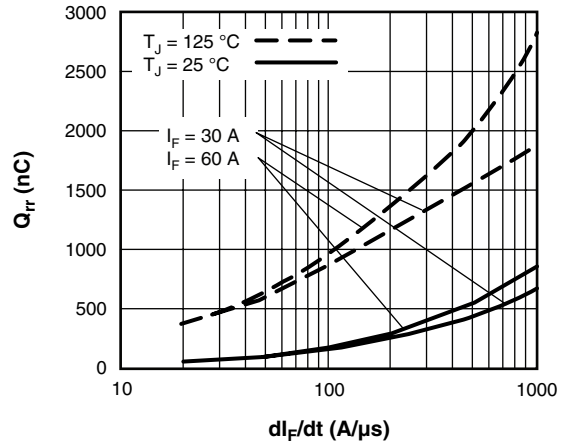


Fig. 7 - Typical Stored Charge vs. di_F/dt

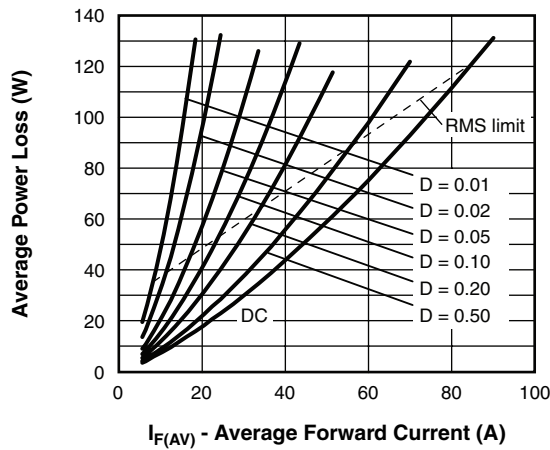


Fig. 6 - Forward Power Loss Characteristics

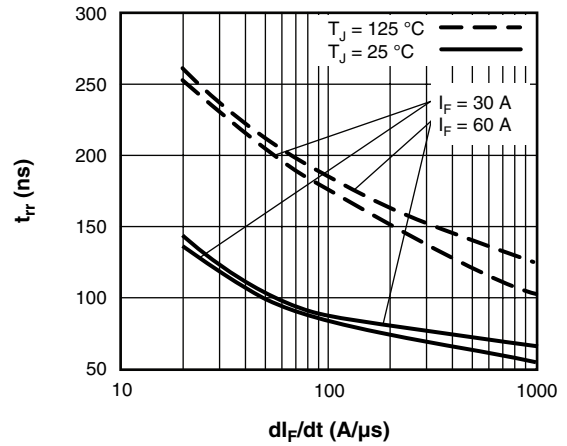


Fig. 8 - Typical Reverse Recovery Time vs. di_F/dt

Note

- (1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
 Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R

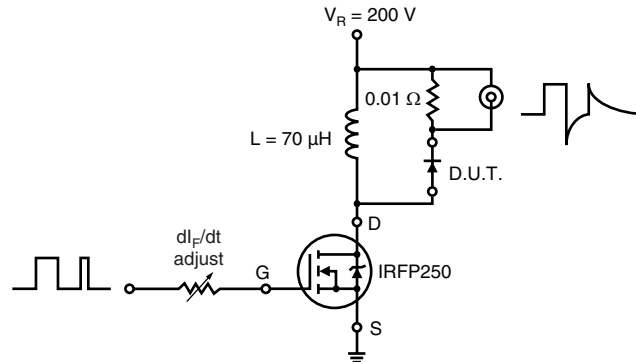
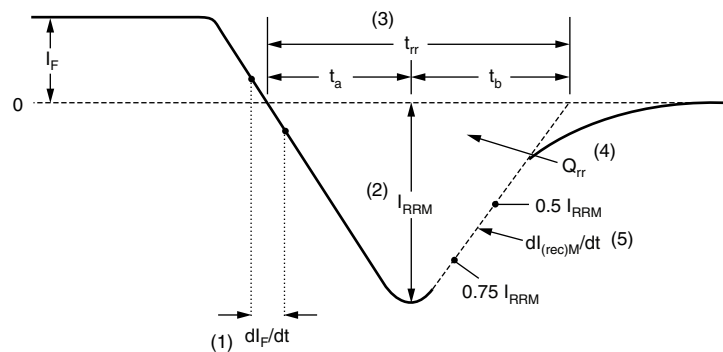


Fig. 9 - Reverse Recovery Parameter Test Circuit



- | | |
|---|---|
| <p>(1) dl_F/dt - rate of change of current through zero crossing</p> <p>(2) I_{RRM} - peak reverse recovery current</p> <p>(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.</p> | <p>(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}</p> $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ <p>(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}</p> |
|---|---|

Fig. 10 - Reverse Recovery Waveform and Definitions

60EPU06/60APU06

Vishay High Power Products

Ultrafast Soft Recovery Diode,
60 A FRED Pt™



ORDERING INFORMATION TABLE

| | | | | | | |
|-------------|-----------|--|----------|----------|-----------|----------|
| Device code | 60 | E | P | U | 06 | - |
| | ① | ② | ③ | ④ | ⑤ | ⑥ |
| | 1 | - Current rating (60 = 60 A) | | | | |
| | 2 | - Circuit configuration: E = Single diode, 2 pins A = Single diode, 3 pins | | | | |
| | 3 | - Package: P = TO-247AC modified | | | | |
| | 4 | - Type of silicon: U = Ultrafast recovery | | | | |
| | 5 | - Voltage rating (06 = 600 V) | | | | |
| | 6 | - • None = Standard production • PbF = Lead (Pb)-free | | | | |

LINKS TO RELATED DOCUMENTS

| | |
|--------------------------|---|
| Dimensions | http://www.vishay.com/doc?95001 |
| Part marking information | http://www.vishay.com/doc?95006 |



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